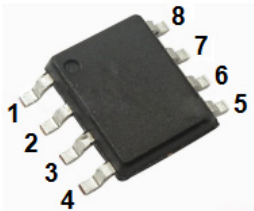
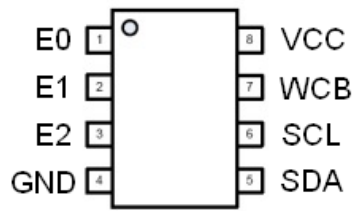


/ Descriptions			
BRCM24C02SC	SOP-8	2 Kbit	I ² C

/ Features			
1.7V	2.5~5.5V	1Mhz	1.7~2.5V
400Khz			
CMOS	400uA	1.6mA	
8			
128			
5ms			
100	100	ESD HBM	6KV
+/-200mA;			

/ Applications

/ Pinning



/ Pinning

Pin	Name	Type	Description
1	E0	Input	
2	E1	Input	
3	E2	Input	
4	GND	Ground	
5	SDA	I/O	/
6	SCL	Input	
7	WCB	Input	
8	VCC	Power	

/ Marking

/ Absolute Maximum Ratings(Ta=25)

			mA
			V

/ Reliability Characteristic

		Ñ				

/ DC Electrical Characteristics(Unless otherwise specified, Vcc = 1.7V to 5.5V, TA = -40°C to 85°C)

		o				
		o				
			-			

/ AC Electrical Characteristics(Unless otherwise specified, Vcc = 1.7V to 5.5V, TA = -40°C to 85°)

		≤			≤ ≤			

/ Functional Description

H / Data Input

SDA SDA SCL (1) SCL
SDA (1)

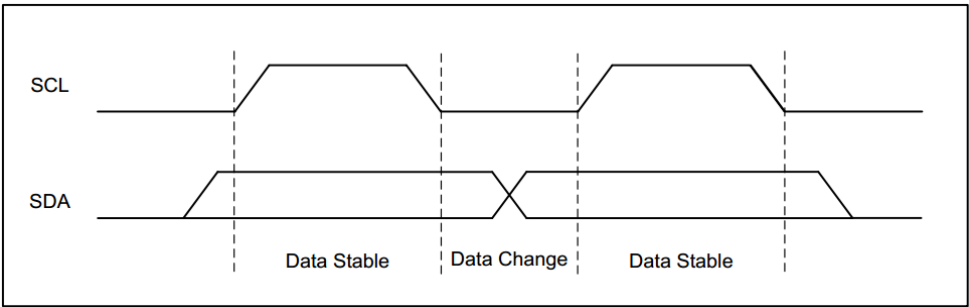


Figure 1 Data Validity

H / Start Condition

SCL SDA
2

H / Stop Condition

SCL SDA
BRCM24C02SC

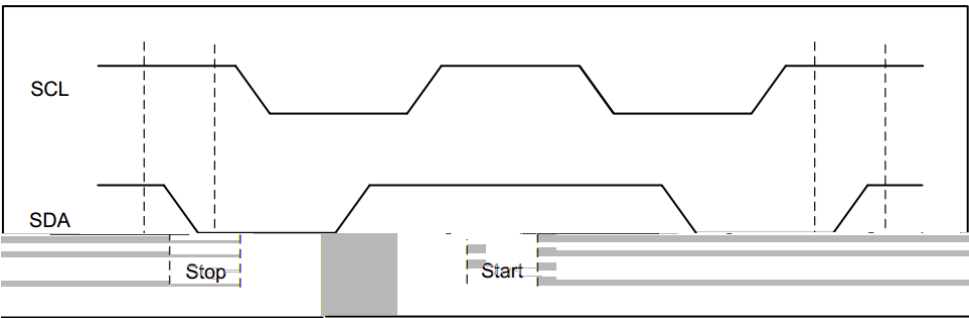


Figure 2 Start and Stop Definition

H ACK / Acknowledge

ACK BRCM24C02SC BRCM24C02SC “ 0 ”
9

/ Functional Description

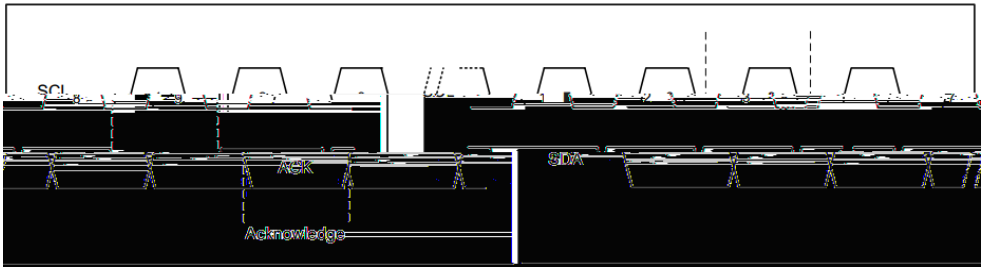


Figure 3 Output Acknowledge

H / Standby Mode

BRCM24C02SC (a) (b)
(c)

H / Soft Reset

(a) (b)
(c) 4

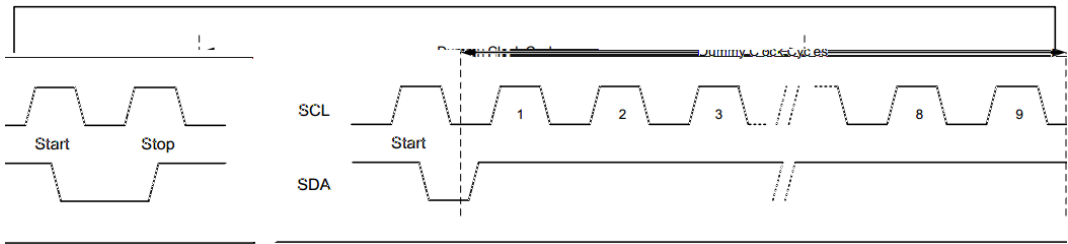


Figure 4 Soft Reset

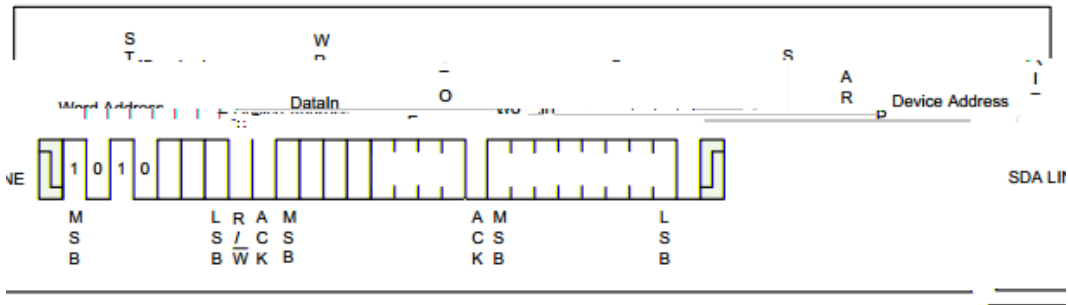
H / Device Addressing

BRCM24C02SC 8 1
1 0

/ Functional Description



/ Functional Description

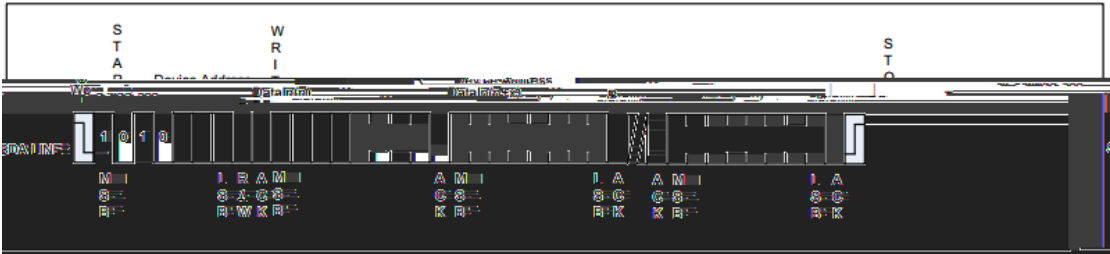


H / Page Write

BRCM24C02SC

" 0 "

BRCM24C02SC



3

BRCM24C02SC

8

/ Functional Description

H / Acknowledge Polling

BRCM24C02SC
/ BRCM24C02SC
“ 0 ”

H / Write Identification Page

16
(a) 1011b
(b) A5 / A4 0 1 A7 / A6 “ 00 ”
(c) A3 / A0
NoACK

H / Lock Identification Page

ID Lock ID
(a) 1011b;
(b) A6 1 ;
(c) xxxx xx1x x 0 1

/ Functional Description

H / Read Operations

/ " 1 "

;

H / Current Address Read

1

/ " 1 "

BRCM24C02SC

" 0 "

7

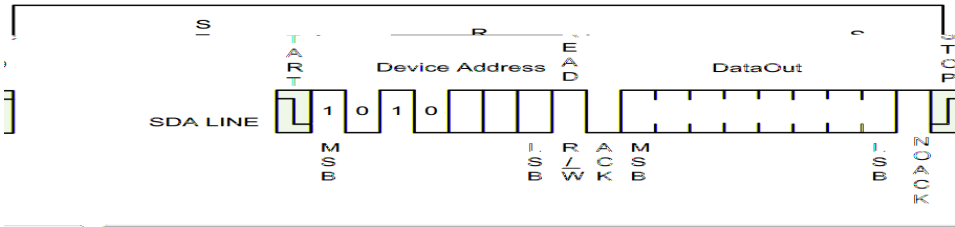


Figure 7

H / Random Address Read

" "

BRCM24C02SC

BRCM24C02SC

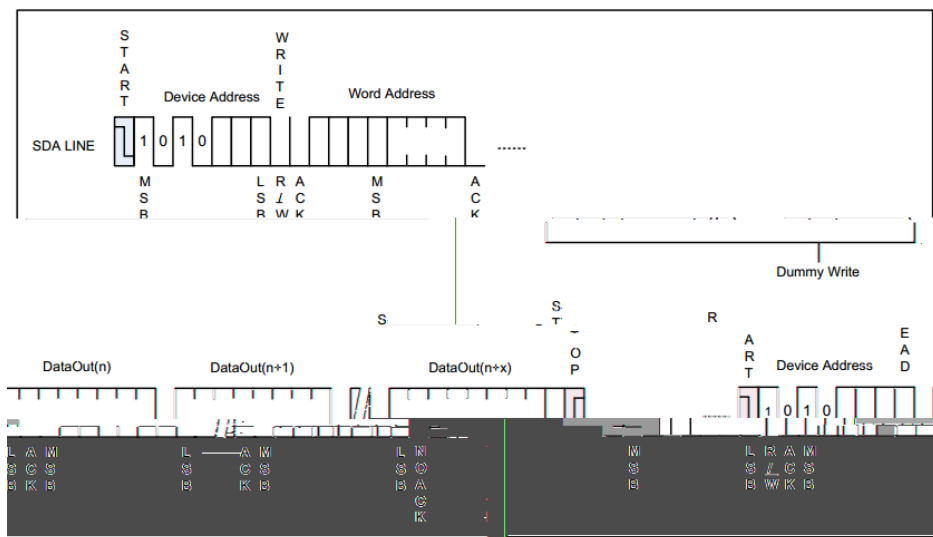
" 0 "

8

The timing diagram illustrates the sequence of operations for the STARC REAST system. It shows the relationship between Word Address, Jump Address, DataOut, and Stack Address signals. The diagram is divided into several sections, each corresponding to a different memory bank or operation. The labels at the bottom indicate the specific memory banks or operations: MSB, LRAM, SLCS, B WKB, A, C, K, M, S, B, LRAM, SLCS, B WKB, L, S, B, N, O, A, C, K. A 'Dummy Write' operation is also indicated.

H / Sequential Read

9



11 17

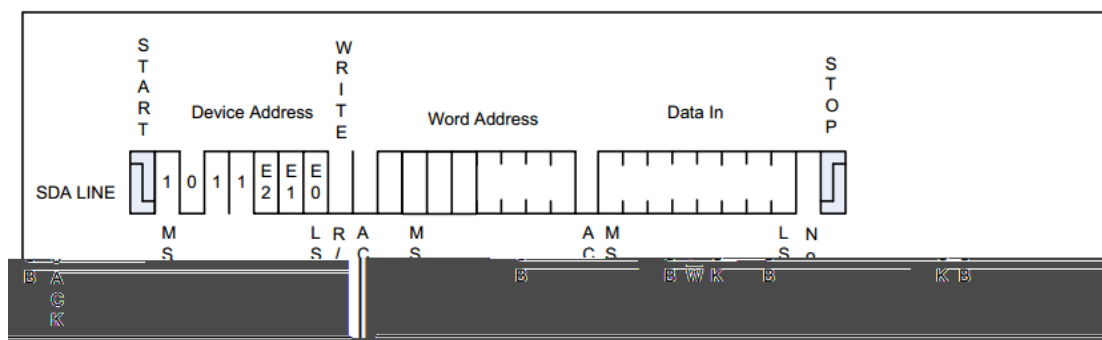
H / Read Identification Page

16

1011b A7 / A6 0 A5 A4 / A0 ID

10d 6 ID

16

$$\frac{[ACK] + [NoACK]}{10}$$


16

128

EEPROM

1

EEPROM

/ Functional Description

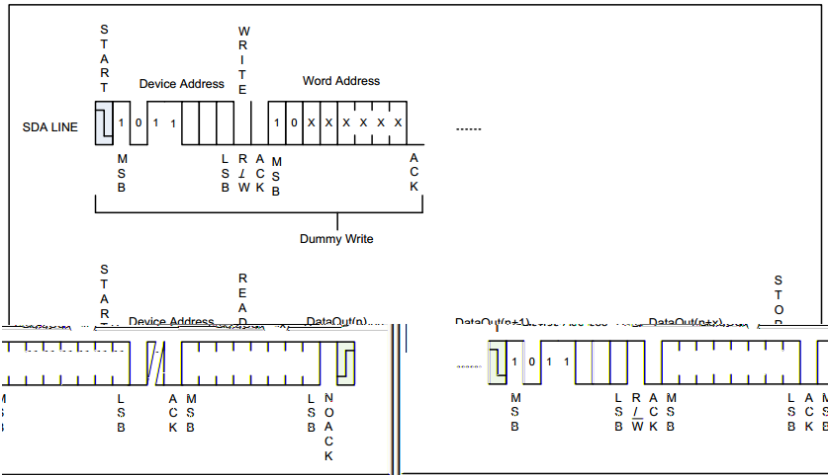
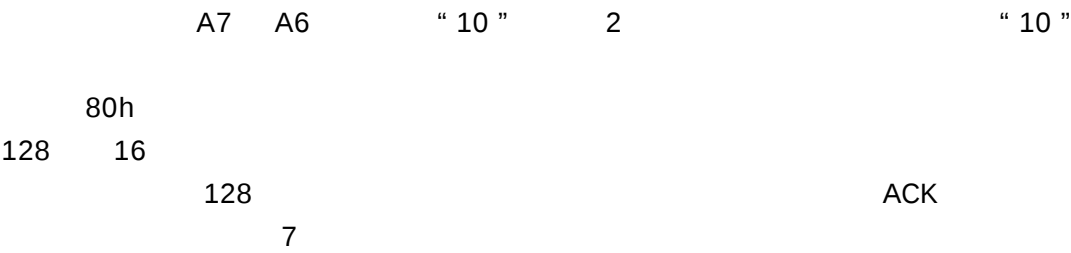
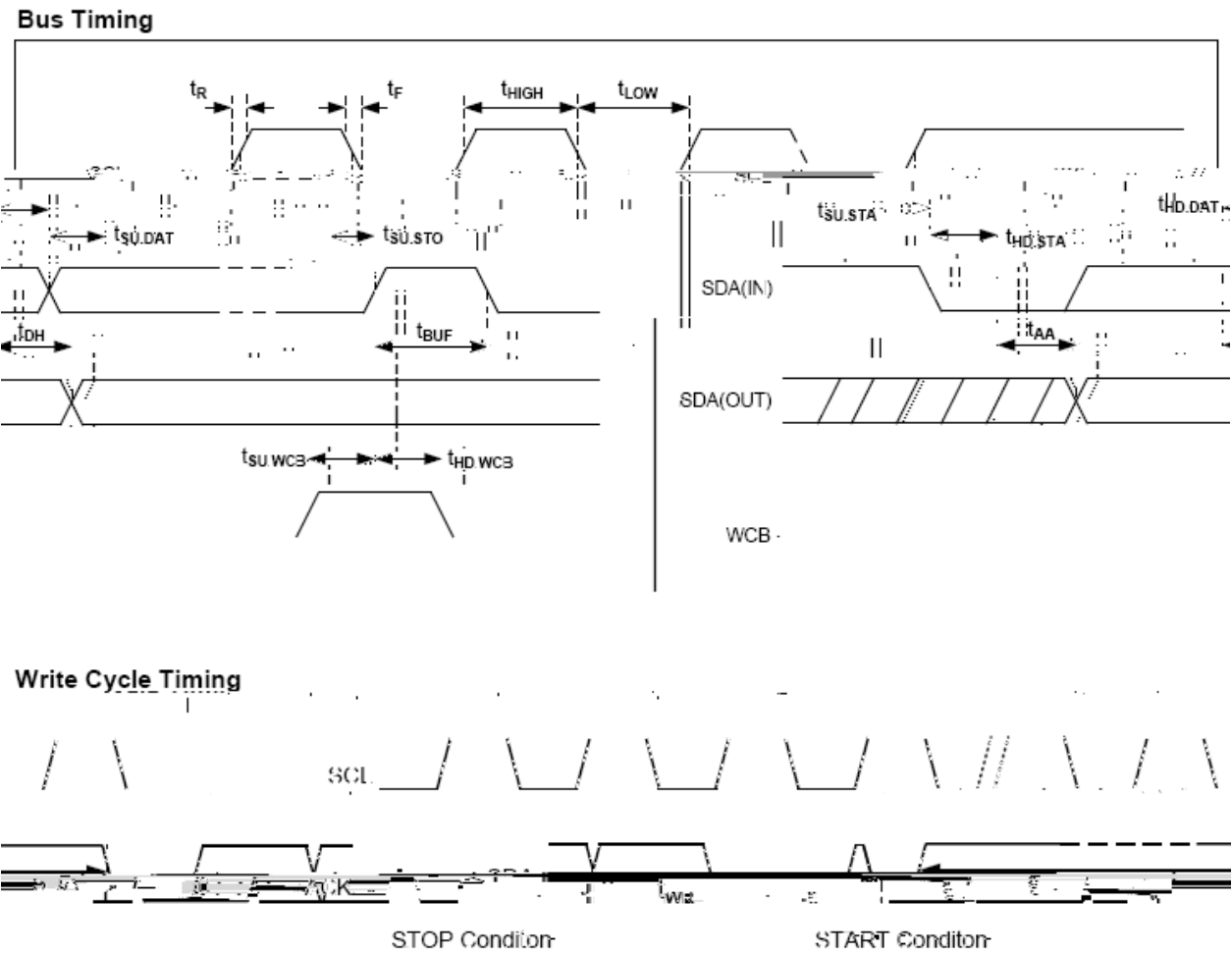


Figure 11 Sequential Read

/ Time Sequence Diagram

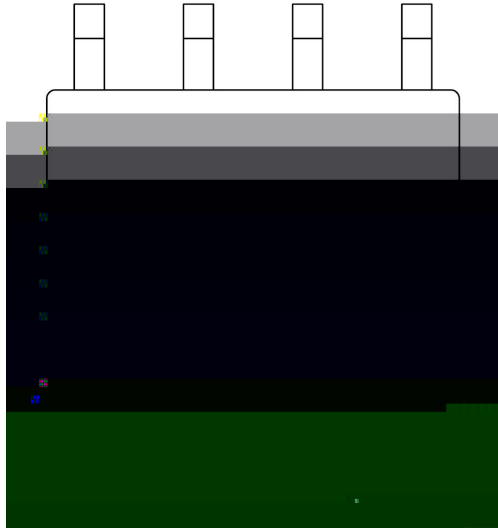


Note: The write cycle time t_{WC} is the time from a valid stop condition of a write sequence to the end of the internal clear/write cycle. No

/ Package Dimensions

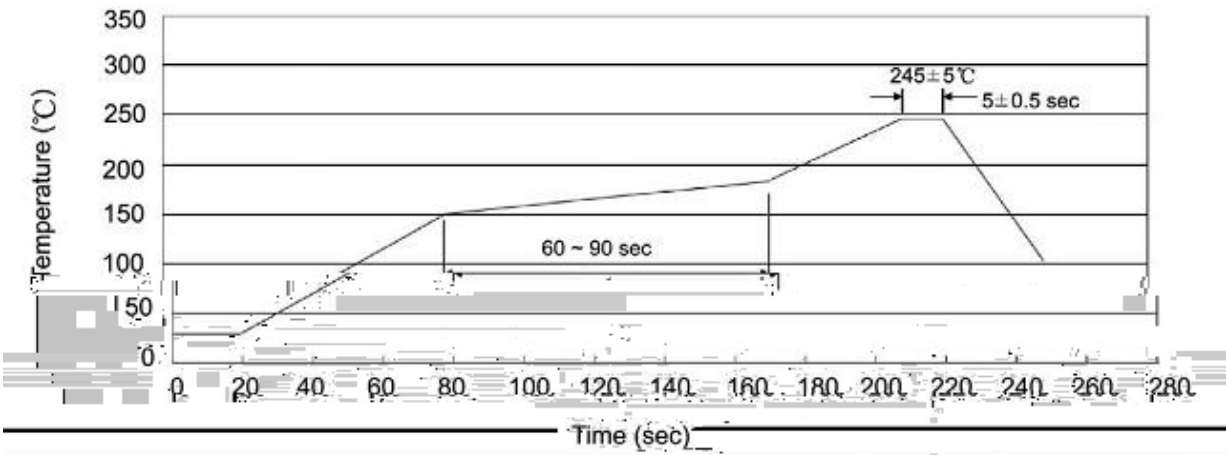


/ Marking Instructions



24C02

() / Temperature Profile for IR Reflow Soldering(Pb-Free)



± ± ± ±

/ Resistance to Soldering Heat Test Conditions

± ± ± ±

/ Packaging SPEC.

	Units/Reel	Reels/Inner Box	Units/Inner Box	Inner Boxes/Outer Box	Units/Outer Box	Reel	Inner Box	Outer Box
SOP/ESOP-8	4,000	2	8,000	6	48,000	13 ×12	360×360×50	380×335×366

/ Notices